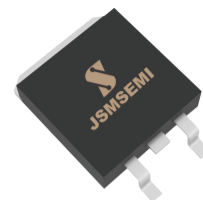


FEATURES

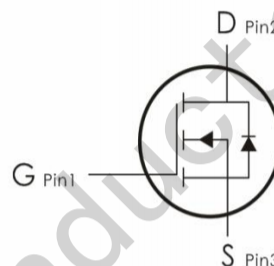
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



TO-263-2L



Device Marking and Package Information		
Device	Package	Marking
IRF740ASTRLPBF	TO-263	IRF740AS

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-263	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DS}	400	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current (note1)	I_{DM}	40	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	96	mJ
Avalanche Current (note1)	I_{AS}	4.4	A
Repetitive Avalanche Energy (note1)	E_{AR}	57	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	63	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
		TO-263	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.5	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	400	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 400V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 5A	--	0.45	0.55	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	1050	--	pF
Output Capacitance	C _{oss}		--	112	--	
Reverse Transfer Capacitance	C _{rss}		--	8	--	
Total Gate Charge	Q _g	V _{DD} = 320V, I _D = 10A, V _{GS} = 10V	--	28	--	nC
Gate-Source Charge	Q _{gs}		--	9	--	
Gate-Drain Charge	Q _{gd}		--	7	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 200V, I _D =10A, R _G = 25 Ω	--	39	--	ns
Turn-on Rise Time	t _r		--	20	--	
Turn-off Delay Time	t _{d(off)}		--	138	--	
Turn-off Fall Time	t _f		--	34	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25 °C	--	--	10	A
Pulsed Diode Forward Current	I _{SM}		--	--	40	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 5A, V _{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 10A, di _F /dt =100A /μs	--	249	--	ns
Reverse Recovery Charge	Q _{rr}		--	1.87	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10.0\text{mH}, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

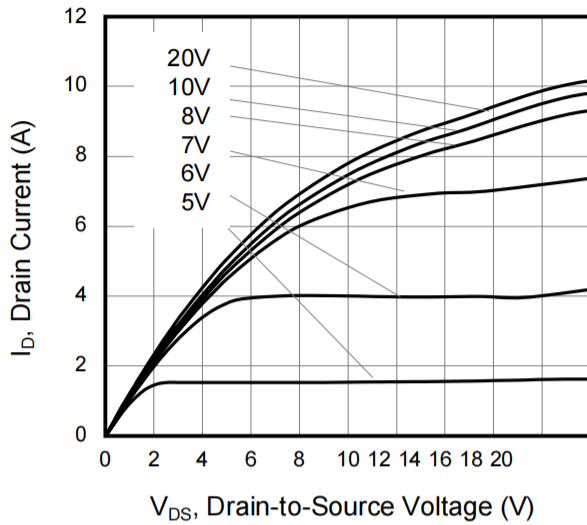


Figure 2. Body Diode Forward Voltage

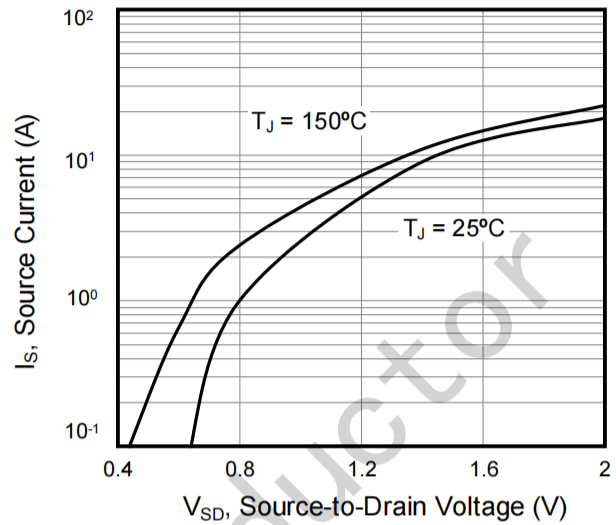


Figure 3. Drain Current vs. Temperature

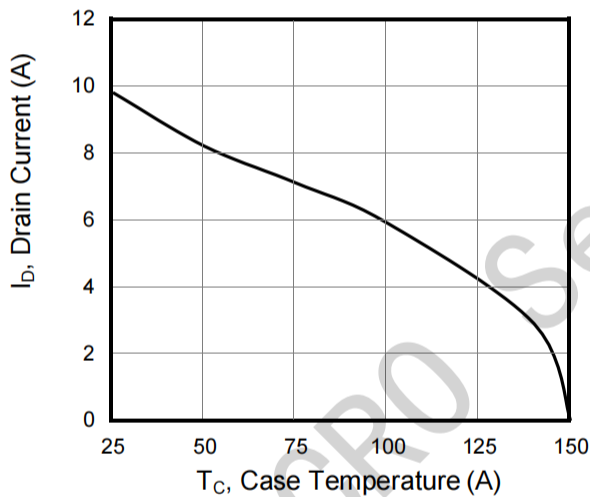


Figure 4. BV_{DSS} Variation vs. Temperature

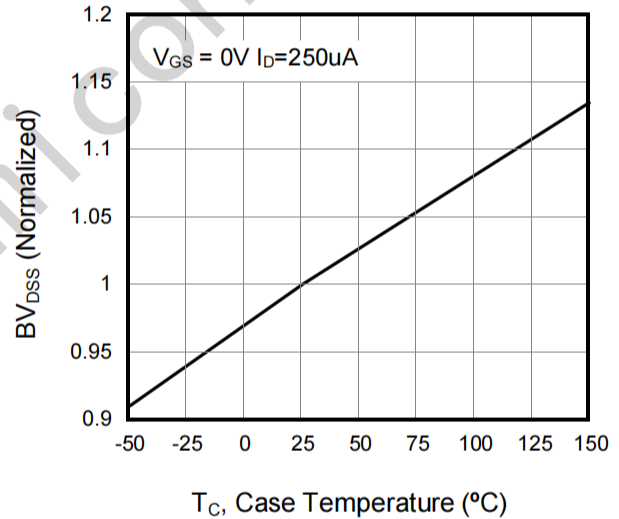


Figure 5. Transfer Characteristics

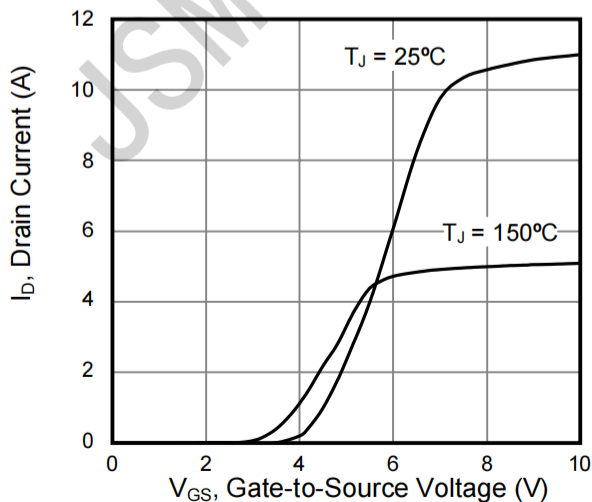
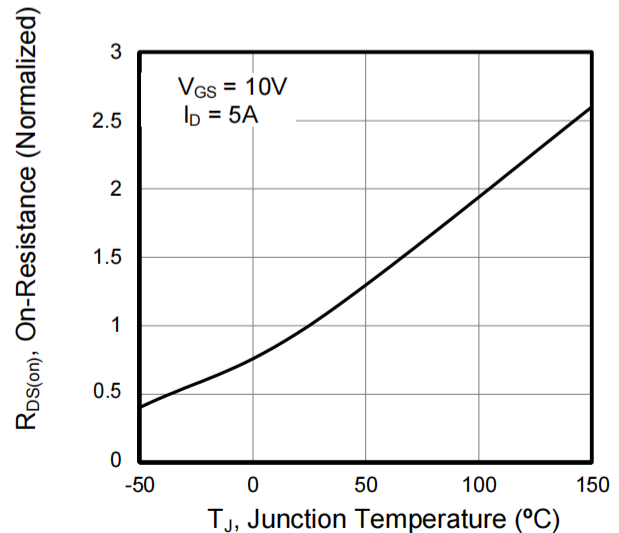


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

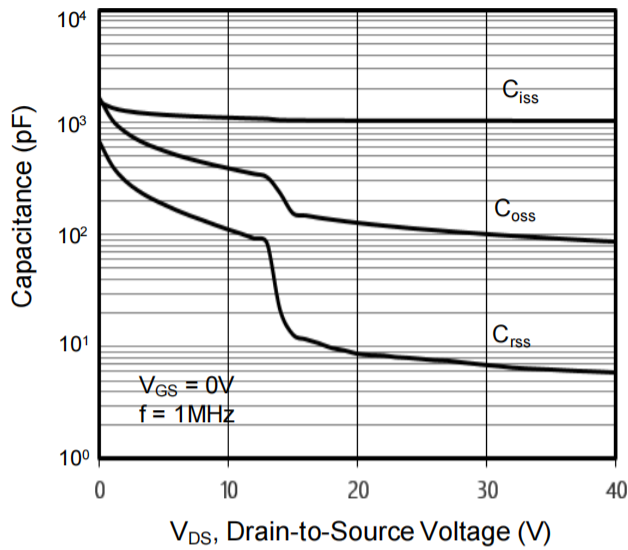


Figure 8. Gate Charge

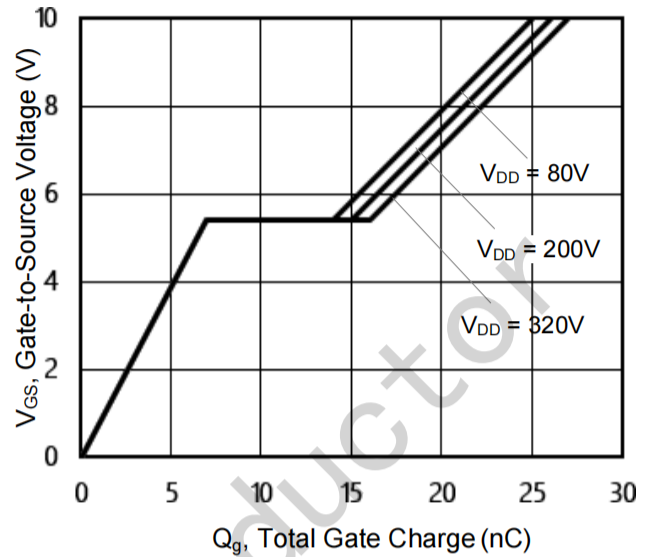


Figure 9. Transient Thermal Impedance

TO-220

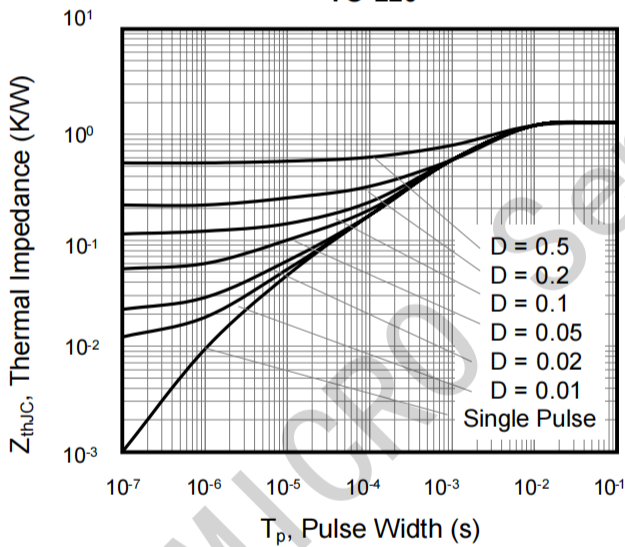


Figure 10. Transient Thermal Impedance

TO-220F

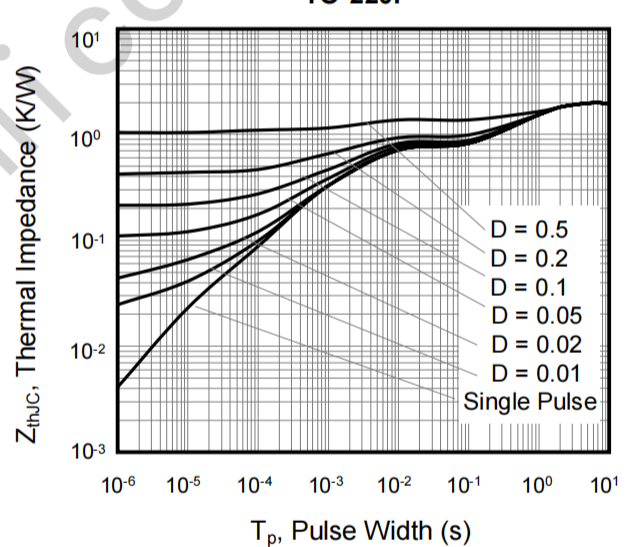


Figure A: Gate Charge Test Circuit and Waveform

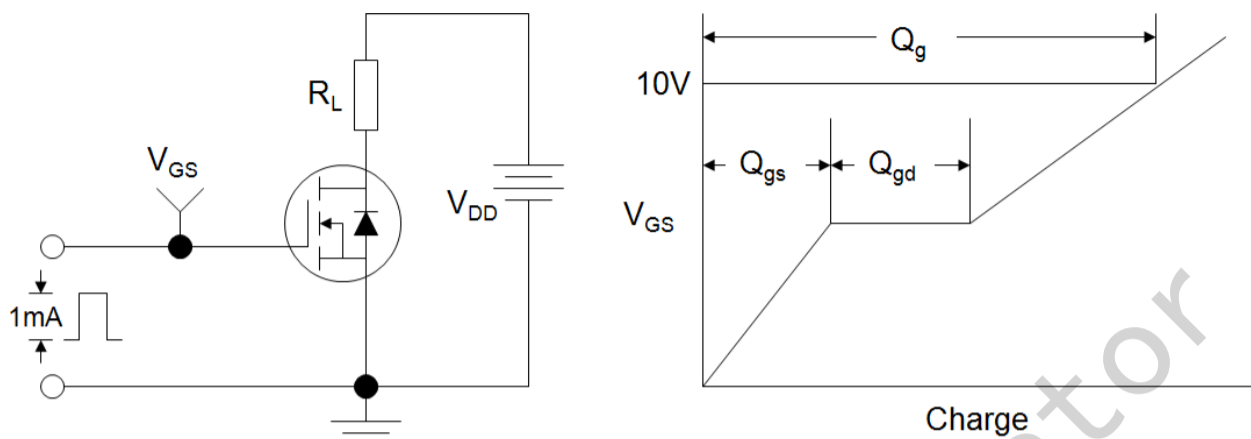


Figure B: Resistive Switching Test Circuit and Waveform

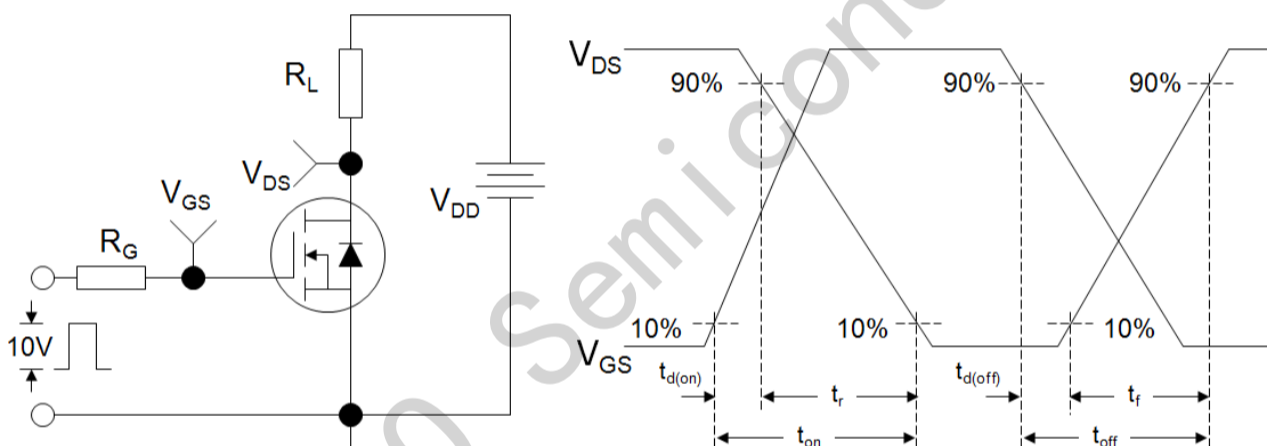
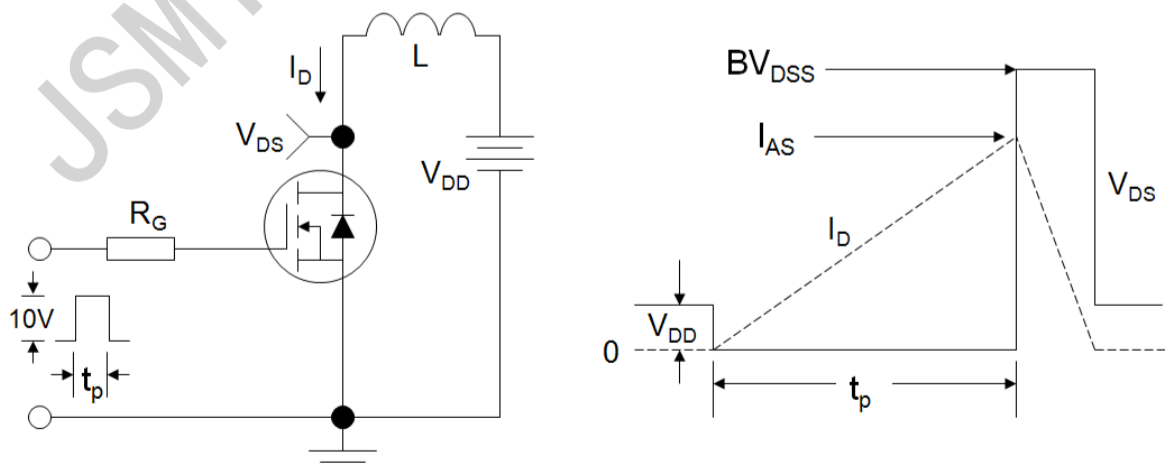
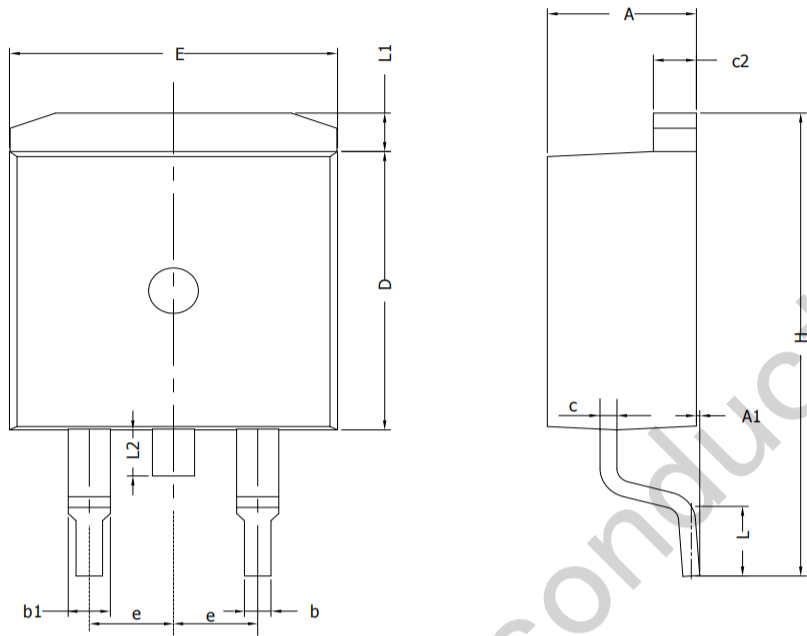


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



Package Outline: TO-263



SYMBOL	MIN	NOM	MAX
A	4.30	4.57	4.72
A1	0	0.10	0.25
b	0.71	0.81	0.91
c	0.30	---	0.60
c2	1.17	1.27	1.37
D	8.50	---	9.35
E	9.80	---	10.45
e	2.54BSC		
H	14.70	---	15.75
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	---	---	1.75

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